503696865 02/17/2016

PATENT ASSIGNMENT COVER SHEET

Electronic Version v1.1 Stylesheet Version v1.2 EPAS ID: PAT3743503

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT

CONVEYING PARTY DATA

Name	Execution Date
THOMAS BERT GORCZYCA	02/16/2016

RECEIVING PARTY DATA

Name:	GENERAL ELECTRIC COMPANY		
Street Address:	1 RIVER ROAD		
City:	SCHENECTADY		
State/Country:	NEW YORK		
Postal Code:	12345		

PROPERTY NUMBERS Total: 1

Property Type	Number
Application Number:	15046184

CORRESPONDENCE DATA

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using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.

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Correspondent Name: GENERAL ELECTRIC COMPANY GLOBAL RESEARCH

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ATTORNEY DOCKET NUMBER:	283667-1 (GERD:1324)
NAME OF SUBMITTER:	JOHN M. RARIDEN
SIGNATURE:	/John Rariden/
DATE SIGNED:	02/17/2016
This document serves as an Oath/Declaration (37 CFR 1.63).	

Total Attachments: 3

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PATENT REEL: 037757 FRAME: 0574 503696865

GE Docket No. 283667-1
SYSTEMS AND METHODS FOR IN-SITU DOPED SEMICONDUCTOR GATE ELECTRODES FOR WIDE BANDGAP SEMICONDUCTOR POWER DEVICES

COMBINED DECLARATION AND GLOBAL ASSIGNMENT FOR UTILITY OR DESIGN PATENT APPLICATION

As the below named inventor(s), I/we hereby declare that:

This declaration and assignment are directed to:

SYSTEMS AND METHODS FOR IN-SITU DOPED SEMICONDUCTOR GATE ELECTRODES FOR WIDE BANDGAP SEMICONDUCTOR POWER DEVICES

	the specification of which	n is attached here	eto OR	
\boxtimes	United States application	or PCT internat	ional application number	
	15/046,184	filed on	February 17, 2016	, as
	amended on [date] (if ap			
	(We hereby authorize and insert above the application	request the Comp number and filing	pany or its delegated attorneys g date of the application when h	s or agents to <nown.)< th=""></nown.)<>

The above-identified application was made or authorized to be made by us.

We believe that we are original joint inventors of a claimed invention in the application.

We hereby acknowledge that any willful false statement made in this declaration is punishable under 18 USC § 1001 by fine or imprisonment of not more than five (5) years, or both.

We acknowledge the duty to disclose information which is material to the patentability of this application as defined in 37 CFR § 1.56, including, for continuation-in-part applications, material information which became available between the filing date of the prior application and the filing date of the continuation-in-part application.

In accordance with our obligation(s) under an Employee Innovation and Proprietary Information Agreement or (as applicable) arising out of other agreements (such as, but not limited to, the Services Agreement between General Electric Company, a New York corporation, and our employers), and/or for other good and valuable consideration of which we acknowledge receipt, we,

Inventor First Name	Inventor Middle Name	Inventor Last Name	Residence Town	Residence State	Residence Country
Thomas	Bert	Gorczyca	Schenectady	NY	US

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PATENT REEL: 037757 FRAME: 0575 GE Docket No. 283667-1

SYSTEMS AND METHODS FOR IN-SITU DOPED SEMICONDUCTOR GATE ELECTRODES FOR WIDE BANDGAP SEMICONDUCTOR POWER DEVICES

hereby sell and assign to:

Name of Company:	General Electric Company
Entity Type:	New York corporation
Address:	1 River Road, Schenectady, New York 12345 USA

herein referred to as "Company", its successors and assigns our entire respective rights, titles and interests in and to the invention and improvements made and conceived by us described in the application(s) listed above and in the following table:

Country of Filing	Type of Filing	Application Number	Filing Date	Title

(We hereby authorize and request the Company or its delegated attorneys or agents to insert above the application number and filing date of the application(s) when known.)

and any and all applications for patent and patents therefrom in any and all countries, including all divisions, continuations, reexaminations and reissues thereof, and all rights of priority resulting from the filing of the application(s), and authorize and request any official whose duty it is to issue patents, to issue any patent on the inventions and improvements resulting therefrom to the Company, or its successors or assigns and agree that on request and without further consideration, we will communicate to the Company or its representatives or nominees any facts known to us respecting the inventions and improvements and testify in any legal proceeding, sign all lawful papers, execute all divisional, continuation, reexamination and reissue applications, make all rightful oaths and generally do everything possible to aid the Company, its successors, assigns, and nominees to obtain and enforce proper patent protection for the invention and its improvements in all countries.

Remuneration claims of the inventor(s)/assignor(s) potentially arising from German Law on Employee Inventions, or any other respective country law, remain unaffected by this assignment.

GE Docket No. 283667-1 SYSTEMS AND METHODS FOR IN-SITU DOPED SEMICONDUCTOR GATE ELECTRODES FOR WIDE BANDGAP SEMICONDUCTOR POWER DEVICES **INVENTOR 1** Date: _____ Signature: Thomas Bert Gorczyca Witnessed by: ______Signature Date: _____ Printed Name of Witness Witnessed by: ______Signature Date: _____ Printed Name of Witness SECTION BELOW IS FOR USE ONLY IF SIGNING IN PRESENCE OF A NOTARY 10 mm/121 Derry Date: 02/16/2016 STATE OF NEW YORK
COUNTY OF Schoulta dy ss assignment, who acknowledged to me that he/she executed the same of his/her own free will for the purposes therein set forth. Seal

STEPHANIE R ROSS NOTARY PUBLIC STATE OF NEW YORK ALBANY COUNTY LIC. #01RO4691974 ²⁰17

COMM. EXP JULY 31/8818-

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